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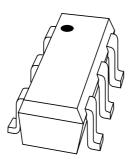
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

## DISCRETE SEMICONDUCTORS

# DATA SHEET



# PUMT1 PNP general purpose double transistor

Product data sheet Supersedes data of 1999 Apr 14 2001 Dec 19



# PNP general purpose double transistor

PUMT1

#### **FEATURES**

- Low current (max. 100 mA)
- Low voltage (max. 40 V)
- Reduces number of components and boardspace.

#### **APPLICATIONS**

• General purpose switching and amplification.

#### **DESCRIPTION**

Two independently operating PNP transistors in an SC-88; SOT363 plastic package. NPN complement: PUMX1.

#### **MARKING**

TYPE NUMBER	MARKING CODE		
PUMT1	FtF		

#### **PINNING**

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
3, 6	collector	TR2; TR1	

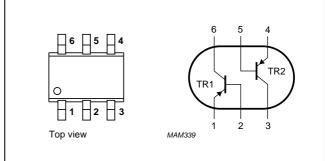


Fig.1 Simplified outline (SC-88; SOT363) and symbol.

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per transist	Per transistor					
$V_{CBO}$	collector-base voltage	open emitter	_	-50	V	
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-40	V	
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-5	V	
I <sub>C</sub>	collector current (DC)		-	-100	mA	
I <sub>CM</sub>	peak collector current		_	-200	mA	
I <sub>BM</sub>	peak base current		_	-200	mA	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	_	200	mW	
T <sub>stg</sub>	storage temperature		-65	+150	°C	
Tj	junction temperature		_	150	°C	
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C	
Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	300	mW	

#### Note

1. Device mounted on an FR4 printed-circuit board.

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# PNP general purpose double transistor

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#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per device				
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	416	K/W

#### Note

1. Device mounted on an FR4 printed-circuit board.

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transist	or				
I <sub>CBO</sub>	collector cut-off current	$I_E = 0; V_{CB} = -30 \text{ V}$	_	-100	nA
		$I_E = 0$ ; $V_{CB} = -30 \text{ V}$ ; $T_j = 150 ^{\circ}\text{C}$	_	-10	μΑ
I <sub>EBO</sub>	emitter cut-off current	$I_C = 0; V_{EB} = -4 \text{ V}$	_	-100	nA
h <sub>FE</sub>	DC current gain	$I_C = -1 \text{ mA}; V_{CE} = -6 \text{ V}$	120	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = -5 \text{ mA}; \text{ note 1}$	_	-200	mV
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = -12 \text{ V}$ ; $f = 1 \text{ MHz}$	_	2.2	pF
f <sub>T</sub>	transition frequency	$I_C = -2 \text{ mA}; V_{CE} = -12 \text{ V}; f = 100 \text{ MHz}$	100	_	MHz

#### Note

1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

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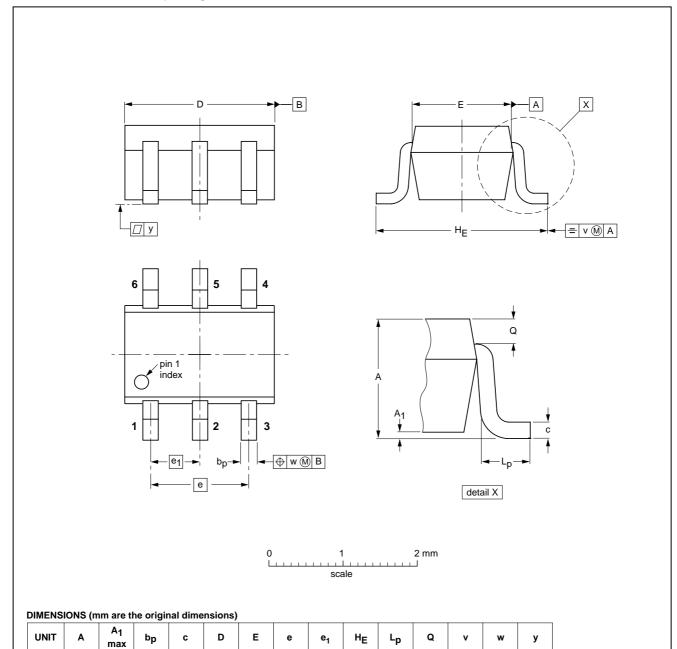
# PNP general purpose double transistor

PUMT1

#### **PACKAGE OUTLINE**

Plastic surface mounted package; 6 leads

**SOT363** 



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT363			SC-88			97-02-28

0.65

0.45 0.15 0.25 0.15

0.2

0.1

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0.25 0.10

0.30

0.20

1.1 0.8

0.1

mm

2.2 1.8 1.35 1.15

1.3

#### PNP general purpose double transistor

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#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

- 1. Please consult the most recently issued document before initiating or completing a design.
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#### **Customer notification**

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#### **Contact information**

For additional information please visit: http://www.nxp.com

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